Interrupt

Refine Search

Search Results -

Terms	Documents
6121164	. 8

Database:

L19

US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Recall Text =

Search:

Clear

Search History

DATE: Monday, June 27, 2005 Printable Copy Create Case

Set Name side by side	Query	<u>Hit</u> <u>Count</u>	Set Name result set
DB=U	SPT; PLUR=YES; OP=OR		
<u>L19</u>	6121164	8	<u>L19</u>
<u>L18</u>	612164	9	<u>L18</u>
<u>L17</u>	6103601	27	<u>L17</u>
<u>L16</u>	61036018	0	<u>L16</u>
<u>L15</u>	6008120	. 36	<u>L15</u>
<u>L14</u>	112 and "single damascene"	1	<u>L14</u>
<u>L13</u>	112 and "atomic percent fluorine"	0	<u>L13</u>
<u>L12</u>	L11 and (("via hole") or (trench))	14	<u>L12</u>
<u>L11</u>	18 and L10	22	<u>L11</u>
<u>L10</u>	usg near4 fsg	86	<u>L10</u>
<u>L9</u>	usg near4 fsgL8	0	<u>L9</u>
<u>L8</u>	fsg NEAR5 SUBSTRATE	102	<u>L8</u>
<u>L7</u>	usg	1239	<u>L7</u>

<u>L6</u>	6861701	1	<u>L6</u>
<u>L5</u>	L3 and ("trench gate" near7 (silicon near3 metal near5 (silicon or silicide)))	3	<u>L5</u>
<u>L4</u>	L3 and "trench gate"	945	<u>L4</u>
<u>L3</u>	power MOSFET	1110305	<u>L3</u>
DB=U	ISOC; PLUR=YES; OP=OR		
<u>L2</u>	L1	0	<u>L2</u>
DB=P	GPB; PLUR=YES; OP=OR		
<u>L1</u>	2003/0178673	0	<u>L1</u>

END OF SEARCH HISTORY